

A METHOD OF BASE FORMATION IN A BICMOS PROCESS

ABSTRACT

[0047] Disclosed is a bipolar complementary metal oxide semiconductor (BiCMOS) or NPN/PNP device that has a collector (112), an intrinsic base (118) above the collector, shallow trench isolation regions (114) adjacent the collector, a raised extrinsic base (202) above the intrinsic base, a T-shaped emitter (800) above the extrinsic base, spacers (700) adjacent the emitter, and a silicide (400) layer that is separated from the emitter by the spacers.